# A Low-Cost, Low-Power Wireless Receiver 

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## Outline

- Motivation
- Introduction to Specifications Design
- Signal Path Design and Experimental Verification
- Synthesizer Design and Experimental Verification
- Final Receiver Design and Measurements


## Motivation



## Basic System Requirements

- Data rate: $1 \mathrm{Mb} / \mathrm{s}$.
- ISM band operation.
- A few channels (>5) for diversity/ multiple access.
- Robust modulation scheme.
- Range ~ 10 m .
- Implementable with very low-cost, low-power devices.


## One Solution: Bluetooth

- State-of-the-art CMOS Bluetooth Radio (Ericsson, ISSCC 2002)

Data Rate: $\mathbf{1} \mathbf{~ M b} / \mathbf{s}$<br>Active Receiver Current $=\mathbf{3 0} \mathbf{~ m A}$<br>Active Transmit Current $=\mathbf{3 5 . 5} \mathbf{~ m A}$<br>Supply Voltage ~ 2.5-3 V<br>Active Radio Area $=4.0$ mm ${ }^{2}$<br>Technology: $0.18 \mu \mathrm{~m}$ CMOS<br>Offchip: Loop filter, SAW filter



Can we make some tradeoffs at the system level to lower costs?

## Build a Simple System (I)

|  | Bluetooth | Zigbee | Zero-G |
| :---: | :---: | :---: | :---: |
| Data Rate | $1 \mathrm{Mb} / \mathrm{s}$ | $250 \mathrm{~kb} / \mathrm{s}$ | $1 \mathrm{Mb} / \mathrm{s}$ |
| Spreading | FHSS, 79 Chan. | DSSS, 32-chip <br> PN code | DSSS, 10-chip <br> offset code |
| Modulation | BFSK | O-QPSK | DBPSK |
| Crystal Offset Tol. | 20 ppm | 80 ppm | 200 ppm |
| Pulse Shaping | Gaussian | Half sine | Gaussian |
| Sensitivity | -70 dBm | -85 dBm | -75 dBm |

- A new approach - concurrent design of circuits and system specifications.


## Build a Simple System (II)

- Choose direct-sequence spreading (DSSS): Frequency Hopping (FHSS) places strict requirements on PLL settling
 time.
- Differential phase-shift keying (DPSK): robust to crystal frequency offset.



## Build a Simple System (III)

- Choose channels: 2400 + $\mathbf{1 2 n} \mathbf{M H z}, n=1 . .6$.

- Relax oscillator phase noise requirement by using large interchannel spacing and guard bands.


## Spectrum Shaping: Offset Coding (I)

- Choose direct conversion: low-power, area-efficient radio architecture.
- DC offset problem at output of mixer. Simple solution: Use large DC-blocking capacitor.

Problem : large capacitor for low cutoff frequency, low noise.


## Spectrum Shaping: Offset Coding (II)

- A solution:

Shape the spectrum away from DC using codingallows smaller capacitor size.


- Additionally, we must use differential encoding for robustness to oscillator frequency offset.


## Spectrum Shaping: Offset Coding (III)

- Example: 4-bit case DC-free spreading case
- Let (1101) and (0010) be spreading symbols for 0 and $\mathbf{1}$, resp.

If previous bit is 0
DC-free diff. encoded sequences: (1001) and (0011), resp.
If previous bit is 1
DC-free diff. encoded sequences: (0110) and (1100), resp.

- Independent of data, ... $\mathbf{x x x} \mathbf{1} \mathbf{x x x} \underline{0} x x \mathbf{1} \mathbf{x x x} \underline{0}$... pattern appears.
- Sharp tones - hard to meet FCC bandwidth requirement.


## Spectrum Shaping: Offset Coding (IV)

- Our solution - introduce periodicity in spreading sequence.
- Example: 4-bit DC-free spreading case
- Let (1010) and (0111) be spreading symbols for 0 and 1, resp.

If previous bit is $\mathbf{0}$
Diff. encoded sequences: (1100) and (0101), resp.
If previous bit is $\mathbf{1}$
Diff. encoded sequences: (0011) and (1010), resp.

- Find such codes which minimize power close to DC.


## Offset Vs. PN codes : Simulated BER



- Chip rate $=10$ Mchips/s, 500 kHz HPF, $\boldsymbol{N}=1000$ samples.


## Receive Signal Path

- Front-end circuits:
- robust to strong out-of-band blockers
- acceptable noise performance with low power consumption



## Receiver Out-of-band Blocking

- Strong signals expected 500 MHz away (from Bluetooth spec.)
- Eliminate off-chip RF preselect filter: linearity and filtering hard.



## Low Noise Amplifier (I)



Andreani et al., "Noise optimization of an inductively degenerated CMOS low noise amplifier", IEEE TCAS II, vol. 48, pp. 835-841, Sept. 2001.



## X-Gate Mixer (I)

- Need greater linearity in presence of strong blockers.
- Expensive to generate very large LO swings at RF.



## X-Gate Mixer (II): DC Simulations





- NMOS - PMOS - Combined


## Mixer Linearity: Measurements (I)

- Prototype mixer \& filters built in $0.25 \mu \mathrm{~m}$ CMOS, tested at 1 GHz .



## Mixer Linearity: Measurements (II)



## Passive Chain: Measurements



## Receive Path Design Summary

- A direct conversion architecture with simple HPF is utilized.
- Offset coding is introduced with differential encoding for spectral shaping.
- The expensive pre-LNA band-select filter is eliminated.
- The X-gate mixer is introduced for linear downconversion.
- A passive chain is utilized for filtering blocker signals post downconversion.
- The passive receive chain (including mixer) has been fabricated and tested at 1 GHz .


## Low-Power Frequency Synthesis

- A critical analog block ...

spectrum of local oscillator

downconverted spectrum



## A Typical Frequency Synthesizer



- High frequency $\boldsymbol{f}_{\boldsymbol{O}}=\boldsymbol{N} \boldsymbol{f}_{\mathbf{I N}}$ generated because of prescaler.
- Loop filter determines the dynamics of the loop.


## Power in Prescaler

- One major source of power consumption: high-frequency prescaler in the synthesizer.

- Regular CMOS digital gates: Power scales as $f C V_{D D}{ }^{2}$.
- How to deal with the high-frequency divider?


## Divide-by-2 in Low-Swing Logic



- lower power consumption
$f C V_{D D} V_{\text {swing }}$, but $\boldsymbol{f}$ remains.


## Analog Regenerative Dividers

- Analog frequency dividers have power $V_{D D} I_{B I A S}$.

- If loop gain is sufficient without injection, feedback system oscillates at $\boldsymbol{f}_{\text {free-run }}$
- Regenerative system tracks $\boldsymbol{f}_{\boldsymbol{f}}$, the injection frequency/phase over some locking range. $\boldsymbol{f}_{\boldsymbol{l}}$ must be close to $\boldsymbol{f}_{\text {free-run }}$.


## Injection-locked Frequency Divider

- A harmonic of $\boldsymbol{f}_{\text {free-run }}$ can also be injected : system is a phaselocked divider.



## Phase Noise of ILFD

- Characteristic first-order time constant $\tau$ : determines the dynamic response, locking range and phase noise of the ILFD.



## A New Oscillator

- We can do even better: eliminate a divide-by-3 circuit at the highfrequency end.
- Oscillator has two outputs: one at $\mathbf{3 \boldsymbol { f } _ { \boldsymbol { O } }}$, and one at $\boldsymbol{f}_{\boldsymbol{O}}$.



## A Multiply-by-3 Ring Oscillator



## Injected Current from One Ring



3 pulses


- Ideally, output spectrum contains only $3 f_{O}$ and its harmonics.
- Due to device mismatch, spurious tones at $\boldsymbol{f}_{\boldsymbol{O}}$ and its harmonics appear.


## Simulated Effect of Stage Mismatch



- Single-ended, three stage ring: Gaussian RV $V_{T}$ and $\beta$ for all NMOS devices

$600 \mathrm{MHz} \quad 900 \mathrm{MHz} \quad 1200 \mathrm{MHz}$


## Output Amplitude



$$
\left|V_{m u I t}\right|=2 I_{D C} R_{P}
$$



$$
\left|V_{m u I t}\right|=\left(\frac{4}{\pi}\right)^{2} I_{D C} R_{P}
$$

- Depends on sharpness of current injection, and DC current.


## Oscillator: Differential Implementation



- Twice the voltage amplitude for twice the current consumption.


## Interstage Coupling

## RING A <br> $V_{D D}$ <br> RING B



## Output Amplitude: Simulation at 900 MHz



- Get $\mathbf{1 0 0} \mathbf{~ m V}$ voltage swing with $I_{D C}=150 \mu \mathrm{~A}$ and $\boldsymbol{R}_{P}=\mathbf{6 0 0} \Omega$.


## Comparison: Ideal LC Oscillator



$$
\left|V_{o s c}\right|=\frac{4}{\pi} I_{D C} R_{P}
$$

- LC oscillator shown would ideally provide 115 mV voltage swing with $I_{D C}=150 \mu \mathrm{~A}$ and $R_{P}=600 \Omega$.


## A Prototype VCO at 900 MHz

- Prototype oscillator built in $0.25 \mu \mathrm{~m}$ CMOS - providing 300 MHz and 900 MHz output frequencies.
- Operates at voltages as low as 1.3 V , while consuming $210 \mu \mathrm{~A}$.



## Synthesizer Design Summary

- The power consumption of the high-frequency prescaler is identified as critical.
- After studying various low-power prescaler design techniques, a new multiplier VCO is introduced.
- A prototype design has been fabricated and tested for 900 MHz operation. It trades off phase noise performance for lower power consumption.


## A Fully-Integrated Receiver at 2.45 GHz



## LO Generation Circuits



## Reference Spurs: Measurements



Required:

- $4 \mathrm{MHz}, 8 \mathrm{MHz}$ spurs, 20 dB below carrier.
- 24 MHz spur, 40 dB below carrier.

Eases charge pump design with 1.8 V supply.



## Phase Noise Measurement



## Blocker Sensitivity



## Performance Summary

| Performance | Achieved | Required |
| :---: | :---: | :---: |
| Passband Noise Fig. (@1.9 GHz) | $8.8 \mathrm{~dB}^{\mathrm{a}}$ | $<18 \mathrm{~dB}$ |
| 1-dB Blocker Compress. Pt. | -15 dBm | $-20 \mathrm{dBm}\left(Q_{i n}=3\right)$ |
| LO Phase Noise @24 MHz | $<-115 \mathrm{dBc} / \mathrm{Hz}$ | $<-111 \mathrm{dBc} / \mathrm{Hz}$ |
| Ref. Spur @24 MHz | -45 dBc | $<-40 \mathrm{dBc}$ |
| Signal Path Current | 3 mA |  |
| Synth. Current @2.45 GHz | 2.5 mA |  |
| LO Buffer Current | 4 mA |  |
| Total Current | 9.5 mA |  |
| Supply Voltage | 1.8 V |  |
| Active Chip Area | 0.66 mm |  |
| Off-chip Components | Inductor (ant.), crystal |  |
| Technology | $0.25 \mu \mathrm{~m} \mathrm{CMOS}$ |  |

a. VGA needed after passive chain - not included in design.

## Receiver Die Photo

- Implemented in $0.25 \mu \mathrm{~m}$ CMOS.



## Receiver Cost-Power Comparison



## Contributions

- Contributed to the concurrent design of the system specifications and circuits for the Zero-G system.
- Implemented a highly-integrated, low-power, low-cost receiver frontend which:
- eliminates the band-select filter.
- linearly downconverts and filters strong blockers.
- implements a low-power synthesizer with a multiply-by-3 oscillator.
- Created and experimentally verified a unified model for injectionlocked frequency dividers.


## Publications

R. J. Betancourt-Zamora, S. Verma, T. H. Lee, "1-GHz and 2.8-GHz CMOS Injectionlocked Ring Oscillator Prescalers," Symposium on VLSI Circuits, June 14-16, 2001.
S. Verma, H. Rategh, and T. H. Lee, "A Unified Model for Injection-Locked Frequency Dividers," IEEE Journal of Solid-State Circuits, Volume 38, Issue 6, June 2003, pp 10151027.
S. Verma, J. Xu, T.H. Lee, "A Multiply-by-3 Coupled-Ring Oscillator for Low-power Frequency Synthesis," Symposium on VLSI Circuits, June 12-14, 2003, pp 189-192.
M. Hamada, S. Verma, J. Xu, T.H. Lee, "Completely DC-free Direct Sequence Spectrum Spreading Scheme for Low Power, Low Cost, Direct Conversion Transceiver," WNCG Wireless Networking Symposium, October 2003.
S. Verma, J. Xu, T.H. Lee, "A Multiply-by-3 Coupled-Ring Oscillator for Low-power Frequency Synthesis," IEEE Journal of Solid-State Circuits, Volume 39, Issue 4, April 2004, pp 709-713
S. Verma, J. Xu, M. Hamada, T.H. Lee, "A Low-Cost, Low-Power Wireless Receiver," IEEE Journal of Solid-State Circuits, under preparation.

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## Phase Noise Requirement



- Required SNR $=\underbrace{-30}_{\text {Signal }} \underbrace{-[10 \log (12 \mathrm{MHz})+L(24 \mathrm{MHz})]}_{\text {Phase Noise from Interferer }}$
$>10 \mathrm{~dB}$
- $L(24 \mathrm{MHz})<-110.8 \mathrm{dBc} / \mathrm{Hz}$


## I-Q Mismatch

- Gain mismatch: for a gain mismatch of $\alpha$, SNR degrades by $\alpha^{2}$.
$-10 \%$ mismatch brings 0.9 dB of SNR degradation.
- Phase mismatch: for a phase mismatch of $\phi$, signal power reduced to $1 /(1+\phi)$ in the worst case.
- $10^{\circ}$ mismatch brings 0.7 dB SNR degradation.


## Receiver In-band Blocking



- Relaxed adjacent and alternate channel requirement.
- Eases phase noise and IIP3 required from the receiver.


## Second/Third-Order Intercept



- IIP3 required is -19 dBm , limited by end buffers.
- IIP2 required is +1 dBm , limited by input symmetry.


## High-Density Capacitors

- Woven structure of M1-M2-M3-M4-M5 lines on top of poly-poly capacitors.



## Receive Path Gain/Power Distribution



| $N F$ | 2.1 dB | 4 dB | 16 dB | 1.5 dB |
| :--- | ---: | ---: | ---: | ---: |
| $\mathrm{G}_{\mathrm{AV}}$ | -2.1 dB | 9 dB | -16 dB |  |

Cumulative NF = 13.9 dB
System NF = 8.8 dB

## PLL Implementation



## LNA Implementation



## Alternate Channel IIP3 (External LO)




## X-Gate Mixer (III): DC Simulations




— NMOS —PMOS —Combined

## Cost/Power Estimation Assumptions

- SAW filter after antenna = \$0.30
- Crystal: +/- 10 ppm = \$0.25; +/- 100 ppm = \$0.15
- T/X Switch = \$0.50
- RF Balun = \$0.05
- Passives = \$0.01 each (ignored)
- Cost of $\mathrm{CMOS}=\mathbf{\$ 0 . 1 0} / \mathbf{m m}^{\mathbf{2}}, \mathrm{SiGe} \mathrm{BiCMOS}=\mathbf{0 . 1 5} / \mathbf{m m}^{\mathbf{2}}$
- Our work :
projected receiver power $=2^{*}\left(9.5 \mathrm{~mA}^{*} 1.8\right)=34.2 \mathrm{~mW}$
projected Si area $=2^{*}\left(0.66 \mathrm{~mm}^{2}\right)=1.3 \mathrm{~mm}^{2}$
No T/X switch, No SAW filter, +/- 100 ppm crystal.


## Output Amplitude: Calculation



Fourier coefficient at $\mathbf{2 N} \pi / \boldsymbol{T}$ :

$$
\left|c_{1}\right|=\frac{N Q}{T} \cdot 2\left[\frac{\sin (N \pi \delta / T)}{(N \pi \delta / T)}\right]^{2}
$$

Using $I_{D C}=N Q / T$ and $Z_{\text {tank }}=R_{P}$,

$$
\left|V_{m u l t}\right|=2\left[\frac{\sin (N \pi \delta / T)}{(N \pi \delta / T)}\right]^{2} I_{D C} R_{P}
$$

